

RF Energy

RF Power is no longer just the carrier of information. At different ISM bands, it can be the source of energy, from heating the food, stimulating a plasma lighting, or exciting a MRI, everywhere in daily life!

In return, it demands RF Power device more rugged and thermally optimized in harsh environments, being much more cost effective ways.

- *--Broadest technology offerings (VDMOS/LDMOS/GaN)*
- *--Standard Packaged transistor and turn-key iModule (Bare die on chip) solution both optional*
- *--Industry leading breakdown voltage ensure high ruggedness*
- *--Patented RFPowerOsc simplify the system design*
- *--Copper flange thermally optimized*
- *--Design from bare die enable harmonic tuning or switch mode amplifier*
- *--Significant cost advantage*

ISM band(MHz)	Transistor	Technology	Voltage(V)	Typical Pout(W)	Test condition	Typical Eff (%)
6/13/27/40/64/128	VTSU01900	VDMOS	100	600	CW	70
	VTSU011K2*2	VDMOS	100	2400	Pulse	65
	MQ051K2V	LDMOS	50	1000	CW	80
325/433	ITCH04200B2	LDMOS	28	200	CW	82
	MK0560V	LDMOS	50	600	CW	75
	MQ051K2V	LDMOS	50	1000	CW	70
915	MQ1060V	LDMOS	50	700	CW	60
	ITCH13200B4*2	LDMOS	32	450	CW	70
1300	ITCH13200B4*2	LDMOS	32	500	CW	65
2450	ITCH24015E2	LDMOS	32	15	CW	64
	ITCH24025E2	LDMOS	32	30	CW	63
	ITCH24180B2	LDMOS	32	200	CW	58
	NW2513	GaN	50	130	CW	72
	NW2513*2	GaN	50	250	CW	70
	NW2513*3	GaN	60	400	CW	69